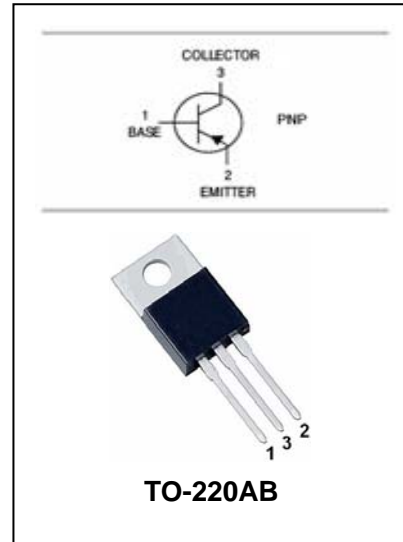


Epitaxial Planar PNP Transistor

TIP42C

2 FEATURES

- Complementary to TIP41C.



MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	DC Pulse	A
		-6 -10	
I_B	Base Current	-2	A
P_C	Collector Dissipation	$T_a=25^\circ\text{C}$	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

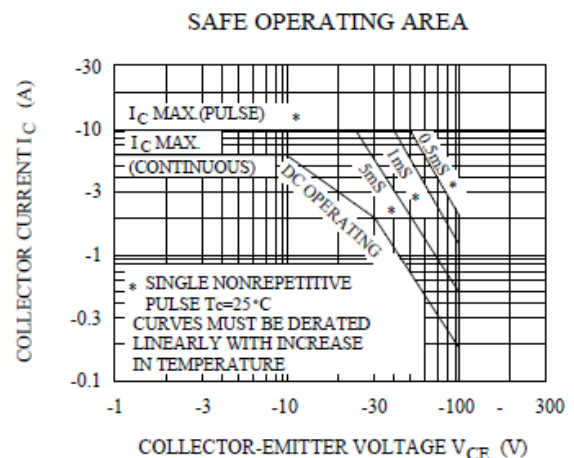
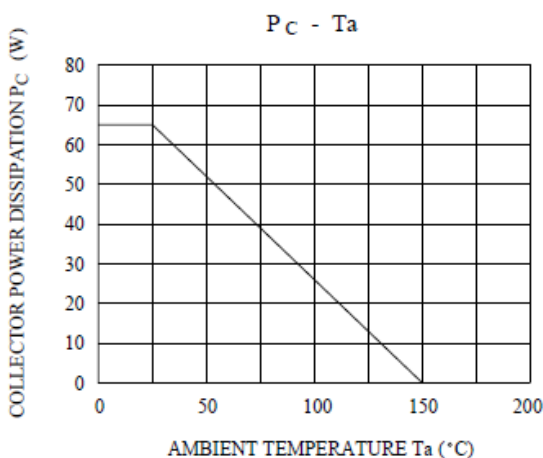
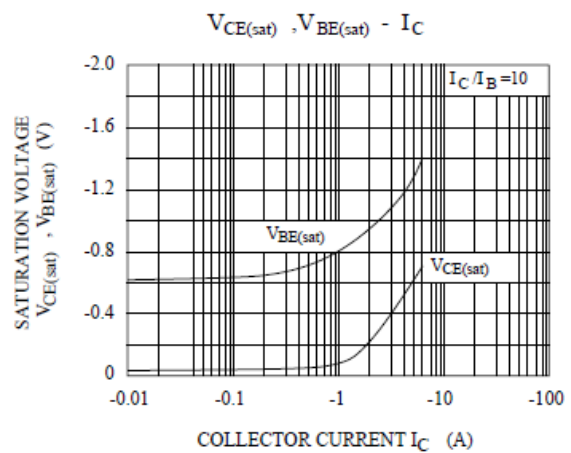
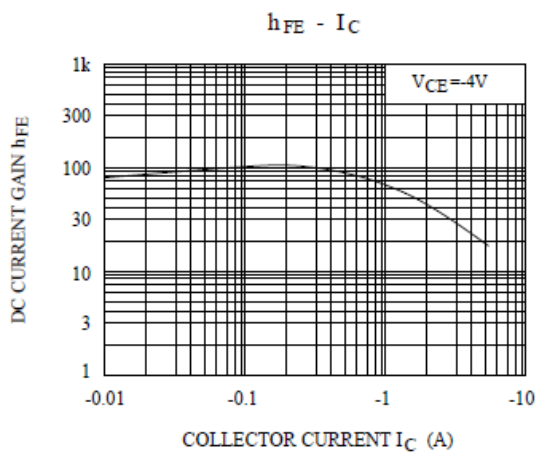
Epitaxial Planar PNP Transistor

TIP42C

ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C = -30mA, I_B = 0$	-100			V
Collector Cut-off Current	I_{CEO}	$V_{CE} = -60V, I_B = 0$			-0.7	mA
Collector Cut-off Current	I_{CES}	$V_{CE} = -100V, V_{EB} = 0$			-400	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-1	mA
DC Current Gain	h_{FE}	$V_{CE} = -4V, I_C = -0.3A$	30			
		$V_{CE} = -4V, I_C = -3A$	15		75	
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -6A, I_B = -600mA$			-1.5	V
Base-emitter on Voltage	$V_{BE(on)}$	$V_{CE} = -4V, I_C = -6A$			-2.0	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -0.5A$	3			MHz

TYPICAL CHARACTERISTICS @ $T_a = 25^\circ C$ unless otherwise specified



Epitaxial Planar PNP Transistor

TIP42C

PACKAGE OUTLINE

Plastic surface mounted package

TO-220AB

